

Atty Docket No. : MART4591-R

Serial No.: 09/759,899

**In the Claims:**

1. (previously withdrawn) A treatment on a silicon oxynitride, which is applicable to a surface of a silicon oxynitride layer covered by a photo resist layer, the treatment comprising the steps of :

using oxygen plasma to remove a majority of the photo resist layer; and

using non-oxygen plasma to overetch in order to remove a residual of the photo resist layer.

2. (previously withdrawn) The method to treat a silicon oxynitride surface according to claim 1, wherein the non-oxygen plasma includes inert gas plasma.

3. (previously withdrawn) The method to treat a silicon oxynitride surface according to claim 2, wherein the non-oxygen plasma includes argon plasma

4. (previously withdrawn) The method to treat a silicon oxynitride surface according to claim 1, wherein a duration of the overetch is approximately 20% to 25% of a duration of the oxygen plasma process.

5. (currently amended) A method to remove a silicon oxide material formed during a removal of a photoresist layer configured above a silicon containing material, and the method in removing the silicon oxide material comprising:

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an oxygen plasma to remove a majority of the photoresist layer, wherein the silicon oxide material is resulted from a reaction between the silicon containing material and the oxygen plasma; and

an overetch process ~~an ion bombardment method~~ using an inert gas plasma to remove a ~~residual~~ remaining of the photoresist layer and to treat the silicon oxide material.

6. (original) The method to remove a silicon oxide material according to claim 5, wherein the inert gas plasma includes an argon gas plasma.

7. (previously withdrawn) A method to remove a photo resist layer, which is applicable to a photo resist layer covering a silicon oxynitride layer, the method to remove the photo resist layer comprising the steps of :

using oxygen plasma to remove a majority of the photo resist layer; and  
using non-oxygen plasma to remove a residual of the photo resist layer.

8. (previously withdrawn) The method to remove the photo resist layer according to claim 7, wherein the non-oxygen plasma includes inert gas plasma.

9. (previously withdrawn) The method to remove the photo resist layer according to claim 8, wherein the inert gas plasma includes argon plasma.

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10. (previously withdrawn) The method to remove the photo resist layer according to claim 7, wherein a duration required for a removal of a residual of the photo resist layer is approximately 20 to 25% of a duration required for a removal of a majority of the photo resist layer.

11. (currently added) The method to remove a silicon oxide material according to claim 5, wherein the overetch process comprises an ion bombardment method.